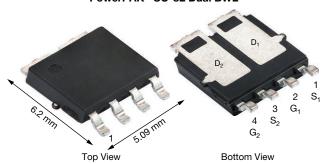


Vishay Siliconix

# Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET

#### PowerPAK® SO-8L Dual BWL

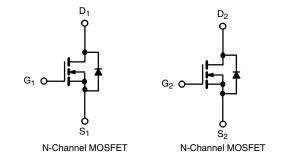


PRODUCT SUMMARY			
V <sub>DS</sub> (V)	40		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0073		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.010		
I <sub>D</sub> (A) per leg <sup>e</sup>	68		
Configuration	Dual		

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATION	
Package	PowerPAK <sup>®</sup> SO-8L
Lead (Pb)-free and halogen-free	SQJ748ELP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	40	V
Gate-source voltage		V <sub>GS</sub>	± 20	V
Continuous drain current e	T <sub>C</sub> = 25 °C <sup>a</sup>		68	
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	39	
Continuous source current (diode conduction) e		I <sub>S</sub>	68	Α
Pulsed drain current b, e		I <sub>DM</sub>	175	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	17	
Single pulse avalanche energy	L = 0.1 IIIII	E <sub>AS</sub>	14	mJ
Maximum power dissipation b, e	T <sub>C</sub> = 25 °C	В	85	W
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	22	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature)			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	52	°C/W
Junction-to-case (drain) d		$R_{thJC}$	2.3	G/VV

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 % b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257)
  d. As per on JESD51-14
- Values based on RthJC and TC of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system.



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PARAMETER	SYMBOL	BOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.2	2.0	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	<u> </u>
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
Drain-source on-state resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0058	0.0073	Ω
		$V_{GS} = 4.5 \text{ V}$	ID = 13 A	-	0.0080	0.0100	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0120	52
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0140	<u> </u>
Forward transconductance b	9fs	V <sub>DS</sub> :	= 15 V, I <sub>D</sub> = 30 A	-	60	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	1081	1514	pF
Output capacitance	Coss	$V_{GS} = 0 V$		-	298	418	
Reverse transfer capacitance	C <sub>rss</sub>			-	37	52	
Total gate charge <sup>c</sup>	$Q_g$		<sub>SS</sub> = 10 V V <sub>DS</sub> = 20 V, I <sub>D</sub> = 15 A	-	19	29	nC
Gate-source charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V		-	4	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$				4	-	]
Gate resistance	$R_g$	f = 1 MHz		1.0	3.0	4.5	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 1.33 $\Omega$ $I_D$ $\cong$ 15 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	4	8	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	20	30	
Fall time <sup>c</sup>	t <sub>f</sub>			-	4	8	
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	175	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 7 A, V <sub>GS</sub> = 0 V		-	0.88	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100A/us		-	21	42	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	8	15	nC
Reverse recovery fall time	t <sub>a</sub>			-	9	-	
· · · · · · · · · · · · · · · · · · ·							ns
Reverse recovery rise time	t <sub>b</sub>			-	13	-	115

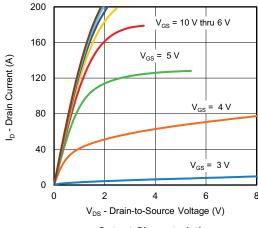
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

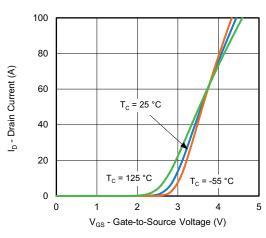


# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

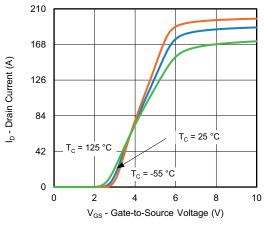




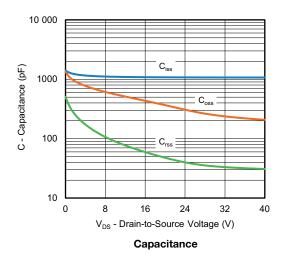


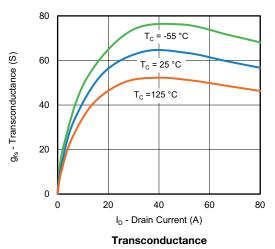


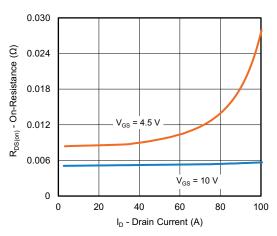
**Transfer Characteristics** 



**Transfer Characteristics** 



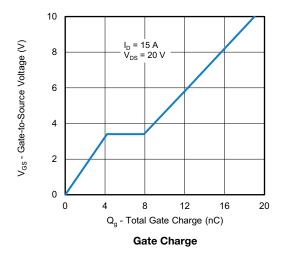


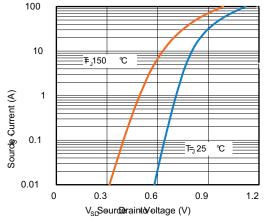


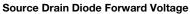
On-Resistance vs. Drain Current

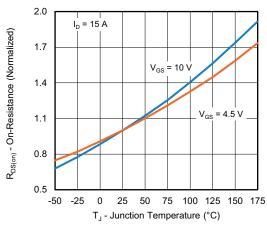


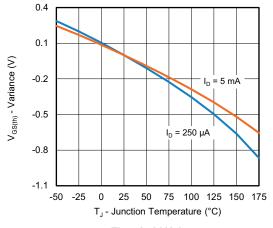
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





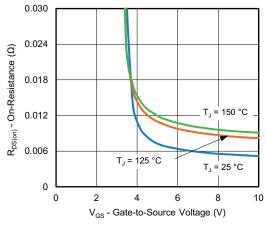


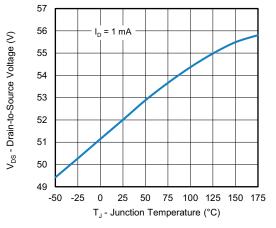




On-Resistance vs. Junction Temperature



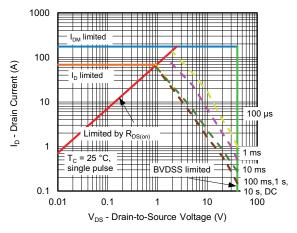




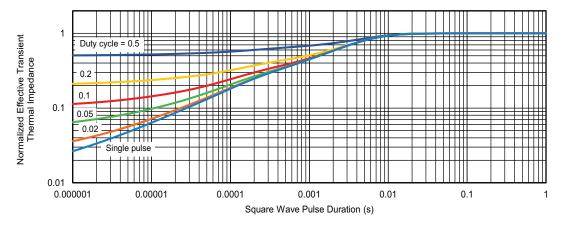
On-Resistance vs. Gate-to-Source Voltage D



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



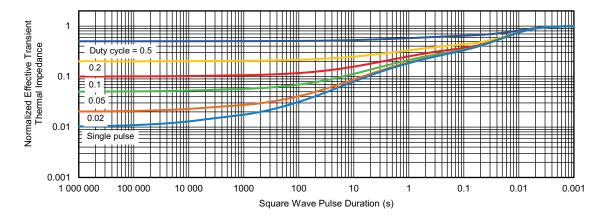
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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